

Description

The DL3342P5S is a bi-directional TVS diode, utilizing leading monolithic silicon technology to provide fast re-sponse time and low ESD clamping voltage, making this device an ideal solution for protecting voltage sensitive high-speed data lines. The DL3342P5S has an ultra-low capacitance with a typical value at 0.6pF, and complies with the IEC 61000-4-2 (ESD) with $\pm 30\text{kV}$ air and $\pm 30\text{kV}$ contact discharge. It is assembled into a DFN2510-10 leadfree package. The small size, ultra-low capacitance and high ESD surge protection make DL3342P5S an ideal choice to protect cell phone, digital video interfaces and other high speed ports.

Features

- ◆ Ultra low capacitance: 0.6pF typical
- ◆ Ultra low leakage: nA level
- ◆ Low operating voltage: 3.3V
- ◆ Low clamping voltage
- ◆ Up to 4 lines protects
- ◆ Complies with following standards:
 - IEC 61000-4-2 (ESD) immunity test
 - Air discharge: $\pm 30\text{kV}$
 - Contact discharge: $\pm 30\text{kV}$
 - IEC61000-4-5 (Lightning) : 12A(8/20 μs)
- ◆ ROHS Compliant

Mechanical Characteristics

- ◆ Package: DFN2510-10 (2.5 x1.0 x0.5mm)
- ◆ Lead Finish: Matte Tin
- ◆ Case Material: "Green" Molding Compound
- ◆ Moisture Sensitivity: Level 3 per J-STD-020
- ◆ Terminal Connections: See Diagram Below
- ◆ Marking Information: See Below

Applications

- ◆ Ethernet 10/100/1000 Base T

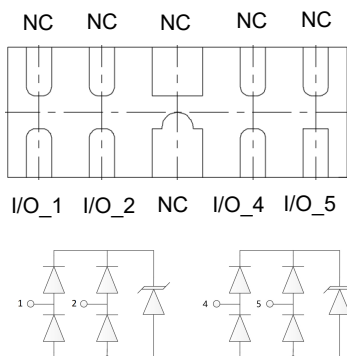
Caution:



This Device is designed for signal line protection only.

Not intended to be used under bias, not for application with a power line.

Dimensions and Pin Configuration



Circuit and Pin Schematic

Marking Information



3342 = Device Marking Code
Dot denotes Pin1

Ordering Information

Part Number	Marking	Packaging	Reel Size
DL3342P5SL	3342	3000/Tape & Reel	7 inch

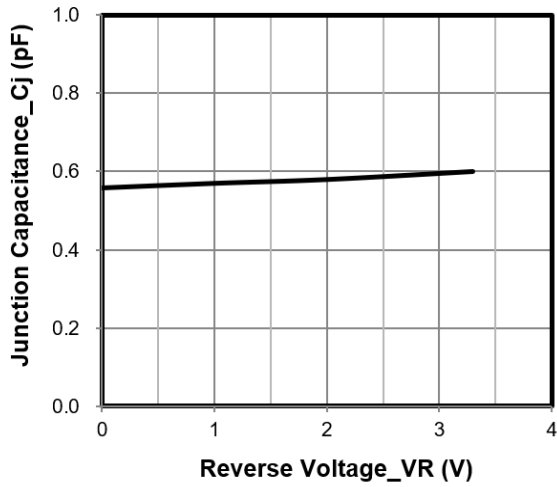
Absolute Maximum Ratings ($T_A=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Peak Pulse Power(8/20 μs)	Ppk	60	W
Peak Pulse Current(8/20 μs)	I _{PP}	12	A
ESD per IEC 61000-4-2 (Air) ESD per IEC 61000-4-2 (Contact)	V _{ESD}	± 30 ± 30	kV
Operating Temperature Range	T _J	-55 to +125	$^\circ\text{C}$
Storage Temperature Range	T _{stg}	-55 to +150	$^\circ\text{C}$

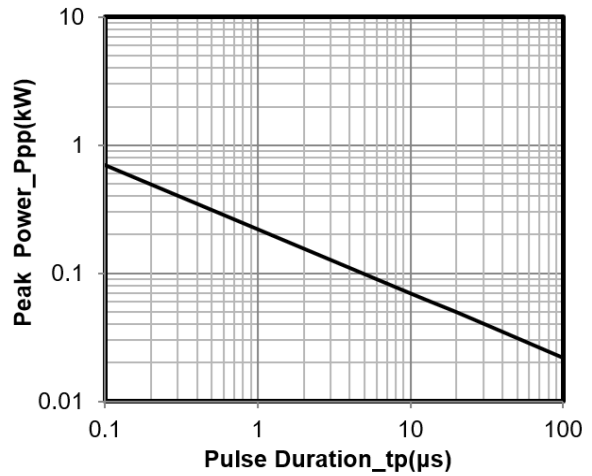
Electrical Characteristics ($T_A=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Working Voltage	V _{RWM}			3.3	V	
Punch-Through Voltage	V _{PT}	3.5			V	I _T = 2 μA
Snap-Back Voltage	V _{SB}	0.8			V	I _T = 50mA
Reverse Leakage Current	I _R			0.2	μA	V _{RWM} = 3.3V
Clamping Voltage	V _C		4		V	I _{PP} = 1A (8 x 20 μs pulse)
Clamping Voltage	V _C		6		V	I _{PP} = 12A (8 x 20 μs pulse)
Junction Capacitance	C _J		0.6		pF	V _R = 0V, f = 1MHz

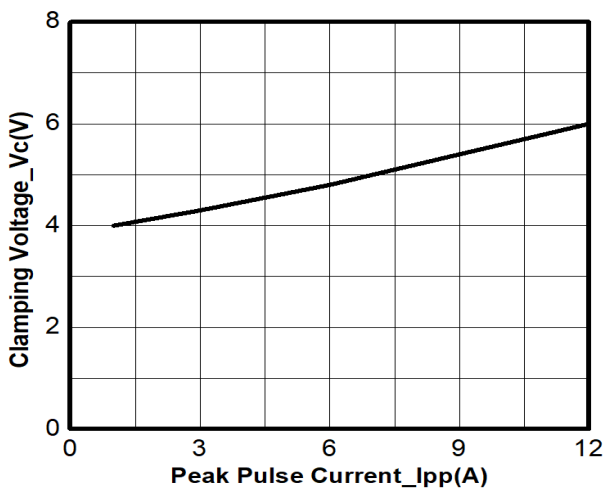
Typical Performance Characteristics (TA=25°C unless otherwise Specified)



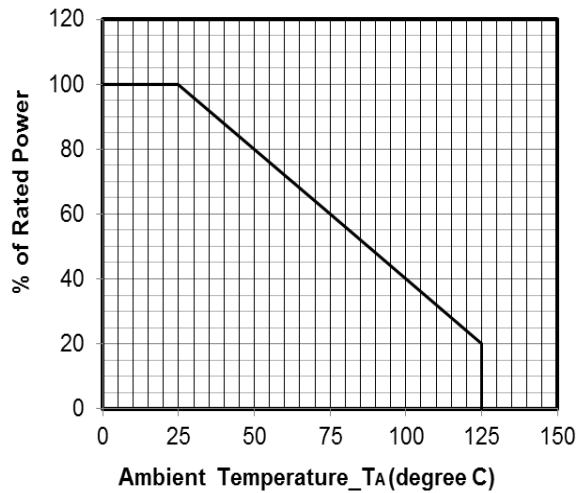
Junction Capacitance vs. Reverse Voltage



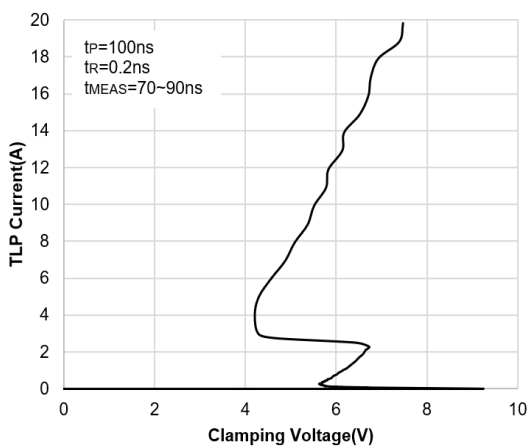
Peak Pulse Power vs. Pulse Time



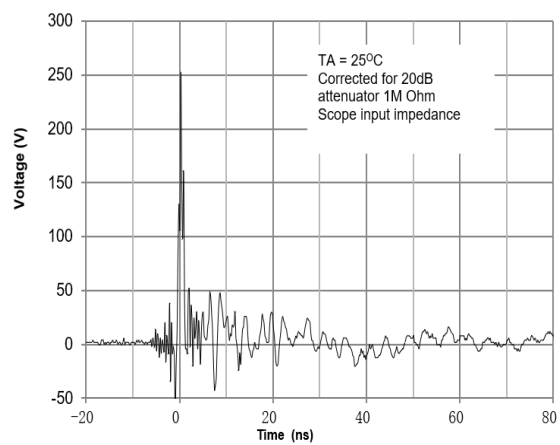
Clamping Voltage vs. Peak Pulse Current



Power Derating Curve



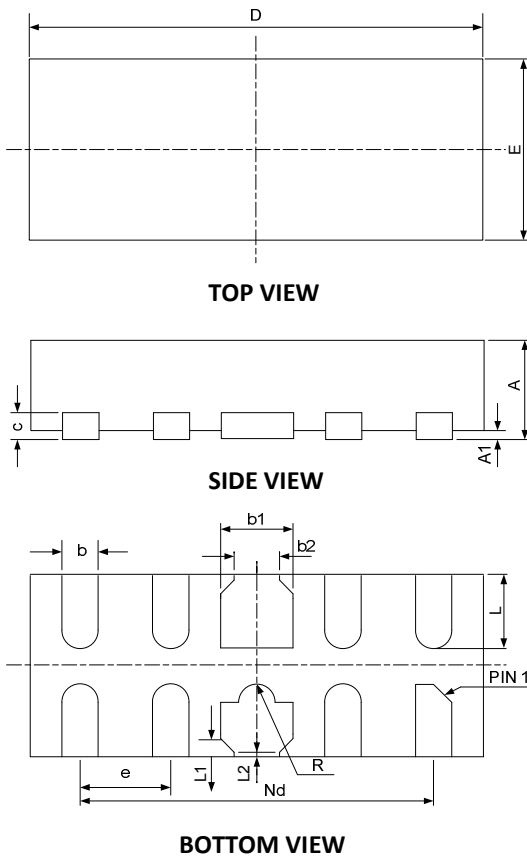
TLP I/V Curve



ESD Clamping Voltage

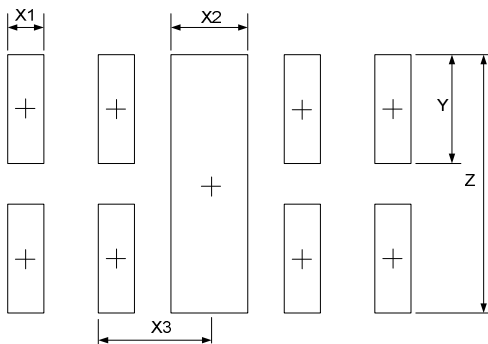
8 kV Contact per IEC61000-4-2

DFN2510-10 Package Outline Drawing



SYM	DIMENSIONS					
	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.45	0.50	0.55	0.018	0.020	0.022
A1	0.00	0.02	0.05	0.000	0.001	0.002
b	0.15	0.20	0.25	0.006	0.008	0.010
b1	0.35	0.40	0.45	0.014	0.016	0.018
b2	0.20	0.25	0.30	0.008	0.010	0.012
c	0.10	0.15	0.20	0.004	0.006	0.008
D	2.45	2.50	2.55	0.098	0.100	0.102
e	0.50BSC			0.020BSC		
Nd	2.00BSC			0.080BSC		
E	0.95	1.00	1.05	0.038	0.040	0.042
L	0.35	0.40	0.45	0.014	0.016	0.018
L1	0.075REF			0.003REF		
L2	0.050REF			0.002REF		
h	0.08	0.12	0.15	0.003	0.005	0.006
R	0.05	0.10	0.15	0.002	0.004	0.006

Suggested Land Pattern



SYM	DIMENSIONS	
	MILLIMETERS	INCHES
X1	0.200	0.008
X2	0.400	0.016
X3	0.500	0.020
Y	0.600	0.024
Z	1.400	0.056

Contact Information

Changzhou D-first Electronics CO.,Ltd.

www.first-electronic.com

Email: xhf@first-electronic.cn

Phone: +86 (0519) -8817 1671